

19. (Amended) A method for fabricating capacitors for semiconductor devices, comprising:

forming a lower electrode on a semiconductor substrate;  
forming a first amorphous TaON thin film directly over the lower electrode;  
annealing the first amorphous TaON thin film in an NH<sub>3</sub> atmosphere;  
forming a second amorphous TaON thin film;  
annealing the second amorphous TaON thin film a first time;  
annealing the second amorphous TaON thin film a second time, thereby forming a TaON dielectric film having a multi-layer structure; and  
forming an upper electrode over the TaON dielectric film.

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20. (Amended) A method for fabricating capacitors for semiconductor devices, comprising:

forming a lower electrode on a semiconductor substrate;  
nitriding an upper surface of the lower electrode in an NH<sub>3</sub> atmosphere;  
forming a first amorphous TaON thin film directly over the lower electrode;  
annealing the first amorphous TaON thin film in an NH<sub>3</sub> atmosphere;  
forming a second amorphous TaON thin film;  
annealing the second amorphous TaON thin film at least once, thereby forming a TaON dielectric film having a multi-layer structure; and  
forming an upper electrode over the TaON dielectric film.

**Please see the attached Appendix for the changes made to effect the above claims.**